RoHS Available

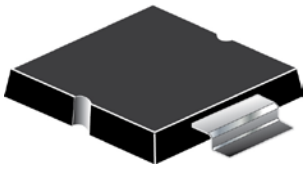
6.5 kW, Unidirectional and Bidirectional TVS Protection Device

High-Reliability screening available in reference to MIL-PRF-19500

DESCRIPTION

These 6.5 kW rated transient voltage suppressors (TVS) in a surface mount PLAD package are provided with design features to minimize thermal resistance and cumulative heating. These devices have the ability to clamp dangerous high voltage, short term transients such as those produced by directed or radiated electrostatic discharge phenomena before entering sensitive component regions of a circuit design. Typical applications include lighting and automotive load dump protection. They are particularly effective at meeting the multi-stroke lightning standard RTCA DO-160, section 22 for aircraft design. This efficient low profile package design is offered in standoff voltage selections (V_{WM}) of 10 volt to 48 volts in either unidirectional or bidirectional construction. This product addition expands High reliable PLAD product portfolio. For more information on PLAD products, broad range of TVS devices please visit our website.

Important: For the latest information, visit our website http://www.microsemi.com.



mini-PLAD
(The cathode is the heatsink under the body of this device.)

FEATURES

- Available in both unidirectional and bidirectional construction (bidirectional with CA suffix).
- High reliability with wafer fabrication and assembly lot traceability.
- All parts surge tested.
- Low profile surface mount package.
- Optional upscreening is available with various screening and conformance inspection options based on MIL-PRF-19500. Refer to Hi-Rel Non-Hermetic Products brochure on our web site for more details on the screening options.
- Suppresses transients up to 6,500 W @ 10/1000 µs (see figure 1).
- Moisture classification is Level 1 with no dry pack required per IPC/JEDEC J-STD-020.
- 3σ lot norm screening performed on standby current (I_D).
- RoHS compliant (2002/95/EC) devices available.
- Halogen free (IEC 61249-2-21)

APPLICATIONS / BENEFITS

- Protection from switching transients and induced RF.
- Protection from ESD, and EFT per IEC 61000-4-2 and IEC 61000-4-4.
- Secondary lightning protection per IEC 61000-4-5 with 42 ohms source impedance:
  Class 1,2,3,4,5: MPLAD6.5KP10A to 48CA
- Secondary lightning protection per IEC 61000-4-5 with 12 ohms source impedance:
  Class 1,2,3,4: MPLAD6.5KP10A to 48CA
- Secondary lightning protection per IEC 61000-4-5 with 2 ohms source impedance:
  Class 2,3: MPLAD6.5KP10A to 48CA
  Class 4: MPLAD6.5KP10A to 22CA
- Pin injection protection per RTCA/DO-160F for Waveform 4 (6.4/69 µs at 25 ºC)*:
  Level 1,2,3,4: MPLAD6.5KP10A to 48CA
  Level 5: MPLAD6.5KP10A to 43CA
- Pin injection protection per RTCA/DO-160F for Waveform 5A (40/120 µs at 25 ºC)*:
  Level 1 and 2: MPLAD6.5KP10A to 48CA
  Level 3: MPLAD6.5KP10A to 36CA
  Level 4: MPLAD6.5KP10A to 12CA
- I_{PP} rating of 40.1 amps to 383 amps.
- V_{WM} rating of 10 volts to 48 volts.
- $V_{(BR)(min)}$ range of 11.1 volts to 53.3 volts.
- $V_{C(MAX)}$ rating of 17 volts to 77.4 volts

*See MicroNote 132 for further temperature derating selection.

MSC – Lawrence
6 Lake Street,
Lawrence, MA 01841
Tel: 1-800-446-1158 or
(978) 620-2600
Fax: (978) 689-0803

MSC – Ireland
Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

Website:
www.microsemi.com

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MAXIMUM RATINGS @ 25 °C unless otherwise specified

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-55 to +150	ºC/W
Thermal Resistance Junction-to-Ambient (1)	$R_{\Theta JA}$	50	ºC/W
Thermal Resistance Junction-to-Case	$R_{\Theta JC}$	1.5	ºC/W
Peak Pulse Power @ 10/1000 µs (2)	P_{PP}	6,500	W
$t_{clamping}$ (0 volts to $V_{(BR)}$ min) Unidirectional Bidirectional		<100 <5	ps ns
Forward Clamping Voltage @ 300 Amps (3)	V_{FS}	2.5	V
Forward Surge Current (3)	I_{FSM}	400	A
Solder Temperature @ 10 s	T_{SP}	260	ºC
Rated Average Power dissipation (5) T_A = 25 °C T_C = 100 °C	$P_{M(AV)}$	2.5 (1) 33.3 (4)	W W

Notes:
1. When mounted on FR4 PC board with recommended mounting pad (see pad layout).
2. Also see figures 1 and 2. With impulse repetition rate (duty factor) of 0.05% or less.
3. At 8.3 ms half-sine wave (unidirectional devices only).
4. Case temperature controlled on heat sink as specified.
5. See MicroNote 134 for derating P_{PP} when also applying steady-state power.

MECHANICAL and PACKAGING

- CASE: Epoxy, meets UL94V-0.
- TERMINALS: Tin/lead or matte-tin (fully RoHS compliant) plating.
- MARKING: Part number.
- DELIVERY option: Tape and reel (13 inch).
- See Package Dimensions on last page.

PART NOMENCLATURE

M PLAD 6.5K P 7.0 CA (e3)

Reliability Level*
M
MA
MX
MXL
*(see Hi-Rel Non-Hermetic Product Portfolio)

Package Designation

P_{PP} Rating (W)

RoHS Compliance
e3 = RoHS compliant
Blank = non-RoHS compliant

Polarity
A = Unidirectional
CA = Bidirectional

Reverse Standoff Voltage

Plastic

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SYMBOLS & DEFINITIONS	
Symbol	**Definition**
$I_{(BR)}$	Breakdown Current: The current used for measuring breakdown voltage $V_{(BR)}$.
I_D	Standby Current: The current at the rated standoff voltage V_{WM}.
I_{PP}	Peak Impulse Current: The peak current during the impulse.
$V_{(BR)}$	Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_C	Clamping Voltage: Clamping voltage at I_{PP} (peak pulse current) at the specified pulse conditions (typically shown as maximum value).
V_{WM}	Rated Working Standoff Voltage: The maximum peak voltage that can be applied over the operating temperature range.
$\alpha_{V(BR)}$	Temperature Coefficient of Breakdown Voltage: The change in breakdown voltage divided by change in temperature.

ELECTRICAL CHARACTERISTICS @ 25 ºC unless otherwise stated

DEVICE*	REVERSE STAND-OFF VOLTAGE V_{WM}	BREAKDOWN VOLTAGE $V_{(BR)}$ @ $I_{(BR)}$		MAXIMUM CLAMPING VOLTAGE V_C @ I_{PP}	MAXIMUM STANDBY CURRENT I_D @ V_{WM}	MAXIMUM PEAK PULSE CURRENT (FIG. 2) I_{PP}	MAXIMUM TEMPERATURE COEFFICIENT OF $V_{(BR)}$ $\alpha_{V(BR)}$
	Volts	Volts	mA	Volts	µA	Amps	mV/°C
MPLAD6.5KP10A(e3)	10	11.1 - 12.3	5	17.0	15	383	9
MPLAD6.5KP11A(e3)	11	12.2 - 13.5	5	18.2	10	358	10
MPLAD6.5KP12A(e3)	12	13.3 - 14.7	5	19.9	10	327	11
MPLAD6.5KP13A(e3)	13	14.4 - 15.9	5	21.5	10	302	12
MPLAD6.5KP14A(e3)	14	15.6 - 17.2	5	23.2	10	280	13
MPLAD6.5KP15A(e3)	15	16.7 - 18.5	5	24.4	10	267	15
MPLAD6.5KP16A(e3)	16	17.8 - 19.7	5	26.0	10	250	16
MPLAD6.5KP17A(e3)	17	18.9 - 20.9	5	27.6	10	236	18
MPLAD6.5KP18A(e3)	18	20.0 - 22.1	5	29.2	10	223	19
MPLAD6.5KP20A(e3)	20	22.2 - 24.5	5	32.4	10	202	22
MPLAD6.5KP22A(e3)	22	24.4 - 26.9	5	35.5	10	183	24
MPLAD6.5KP24A(e3)	24	26.7 - 29.5	5	38.9	10	167	27
MPLAD6.5KP26A(e3)	26	28.9 - 31.9	5	42.1	10	154	29
MPLAD6.5KP28A(e3)	28	31.1 - 34.4	5	45.5	10	143	30
MPLAD6.5KP30A(e3)	30	33.3 - 36.8	5	48.4	10	135	35
MPLAD6.5KP33A(e3)	33	36.7 - 40.6	5	53.3	10	123	38
MPLAD6.5KP36A(e3)	36	40.0 - 44.2	5	58.1	10	111	40
MPLAD6.5KP40A(e3)	40	44.4 - 49.1	5	64.5	10	101	45
MPLAD6.5KP43A(e3)	43	47.8 - 52.8	5	69.4	10	93	49
MPLAD6.5KP45A(e3)	45	50.0 – 55.3	5	72.7	10	89	51
MPLAD6.5KP48A(e3)	48	53.3 – 58.9	5	77.4	10	85	54

* See part nomenclature for additional screening prefixes.

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GRAPHS

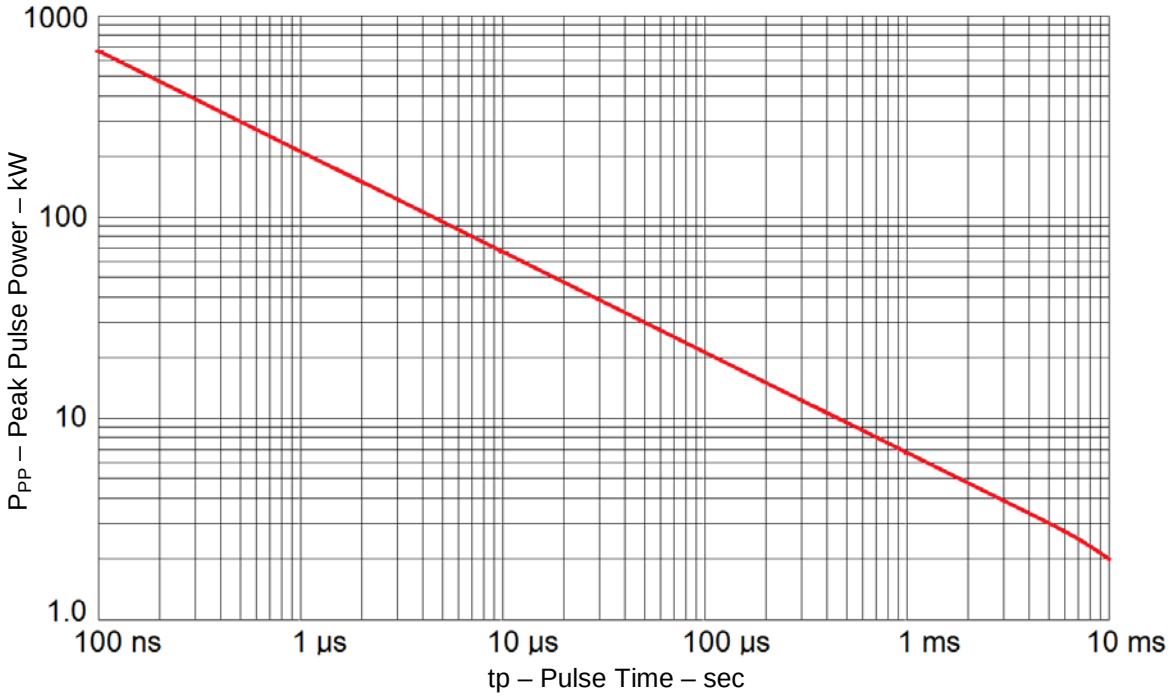
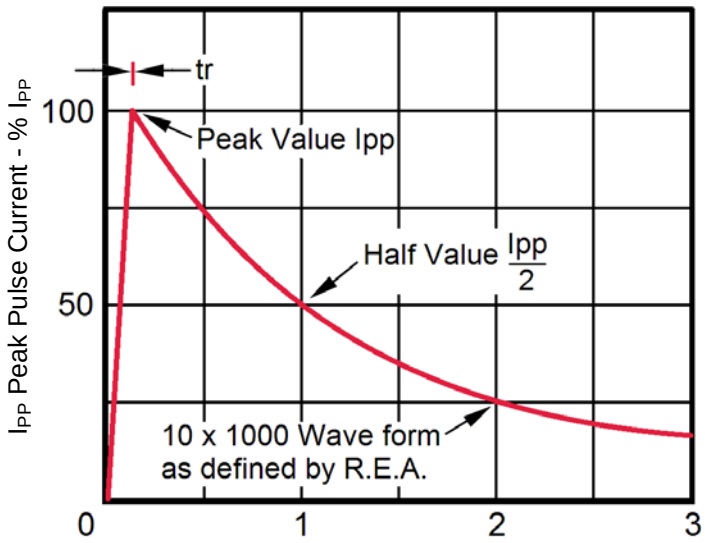


FIGURE 1
Peak Pulse Power vs. Pulse Time
(to 50% of exponentially decaying pulse)



Test waveform parameters: tr = 10 µs, tp = 1000 µs

FIGURE 2
Pulse Waveform

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GRAPHS (continued)

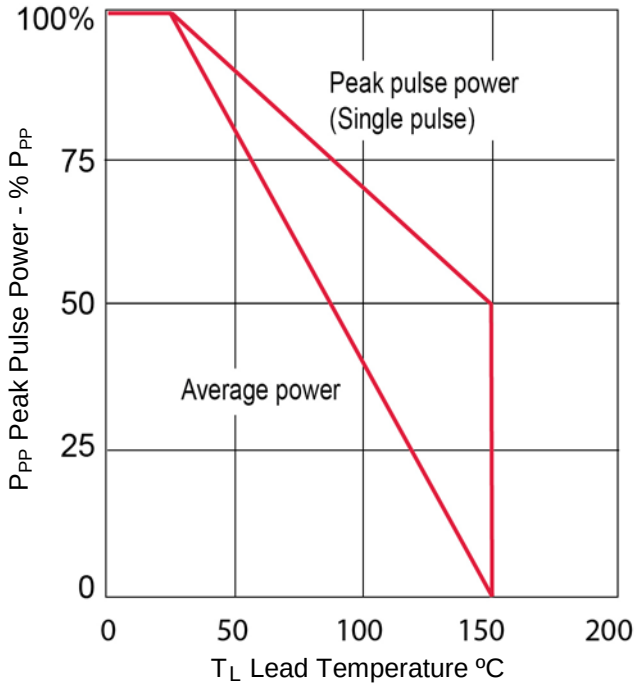

FIGURE 3
Derating Curve

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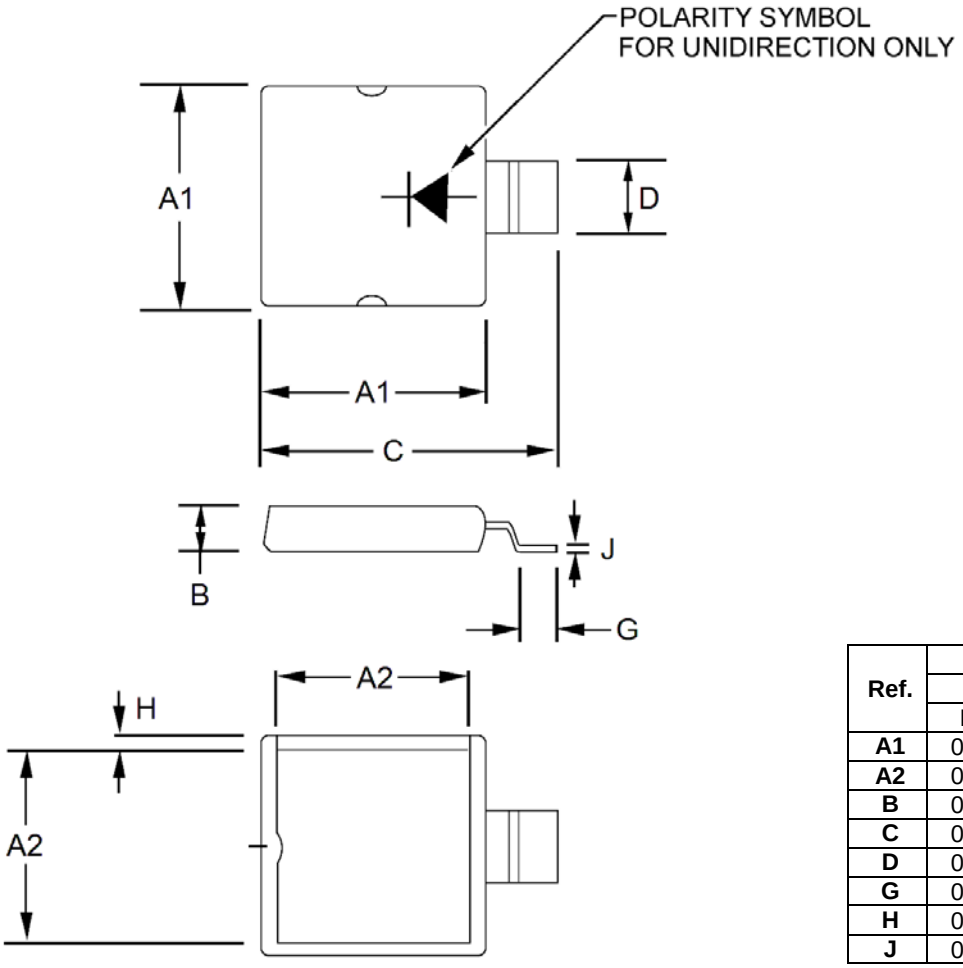
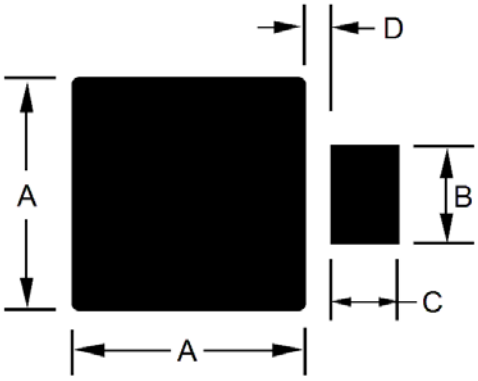
PACKAGE DIMENSIONS



Ref.	Dimensions			
	Inch		Millimeters	
	Min	Max	Min	Max
A1	0.339	0.355	8.61	9.02
A2	0.279	0.295	7.09	7.49
B	0.119	0.135	3.02	3.43
C	0.438	0.454	11.13	11.53
D	0.094	0.110	2.39	2.79
G	0.064	0.080	1.63	2.03
H	0.024	0.040	0.61	1.02
J	0.008	0.012	0.20	0.30

PAD LAYOUT



Ref.	Dimensions	
	Inch	Millimeters
	Typical	Typical
A	0.357	9.08
B	0.117	2.97
C	0.080	2.03
D	0.033	0.84

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